

Product Summary

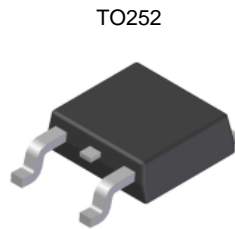
$V_{(BR)DSS}$	$R_{DS(on)}$	I_D $T_C = +25^\circ C$
30V	12m Ω @ $V_{GS} = 10V$	37.8A
	16m Ω @ $V_{GS} = 4.5V$	32.8A

Description

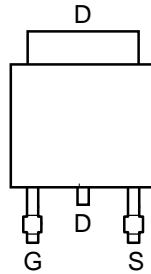
This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

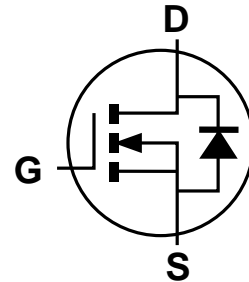
- Backlighting
- DC-DC Converters
- Power Management Functions



Top View



Top View
Pin-Out




Equivalent Circuit

Features

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Note 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

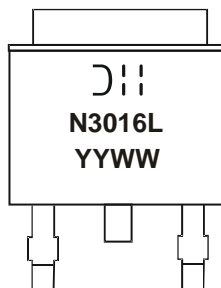
- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.33 grams (Approximate)


Ordering Information (Notes 4)

Product	Case	Packaging
DMN3016LK3-13	TO252	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



 = Manufacturer's Marking
 N3016L = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 14 = 2014)
 WW = Week (01 - 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	12.4 10	A
	Steady State	$T_C = +25^\circ\text{C}$ $T_C = +70^\circ\text{C}$	I_D	37.8 30.3	A
	$t < 10\text{s}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	17 13.6	A
Maximum Body Diode Continuous Current			I_S	2	A
Pulsed Drain Current (10 μs pulse, duty cycle = 1%)			I_{DM}	90	A
Avalanche Current (Note 7) $L = 0.1\text{mH}$			I_{AS}	22	A
Avalanche Energy (Note 7) $L = 0.1\text{mH}$			E_{AS}	24	mJ

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	$T_A = +25^\circ\text{C}$	P_D	1.6	W
	$T_A = +70^\circ\text{C}$		1.0	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	75	$^\circ\text{C/W}$
	$t < 10\text{s}$		34	
Total Power Dissipation (Note 6)	$T_A = +25^\circ\text{C}$	P_D	2.8	W
	$T_A = +70^\circ\text{C}$		1.8	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	46	$^\circ\text{C/W}$
	$t < 10\text{s}$		24	
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	3.1	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	I_{DSS}	—	—	1	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	1.3	—	2.3	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	8	12	m Ω	$V_{GS} = 10V, I_D = 11A$
		—	12	16		$V_{GS} = 4.5V, I_D = 9A$
Diode Forward Voltage	V_{SD}	—	0.70	1.0	V	$V_{GS} = 0V, I_S = 1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	1415	—	pF	$V_{DS} = 15V, V_{GS} = 0V,$ $f = 1.0MHz$
Output Capacitance	C_{oss}	—	119	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	82	—	pF	
Gate Resistance	R_G	—	2.2	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge ($V_{GS} = -10V$)	Q_g	—	25.1	—	nC	$V_{DS} = 15V, I_D = 12A$
Total Gate Charge ($V_{GS} = -4.5V$)	Q_g	—	11.3	—	nC	
Gate-Source Charge	Q_{gs}	—	3.5	—	nC	
Gate-Drain Charge	Q_{gd}	—	3.6	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	4.8	—	ns	$V_{DD} = 15V, V_{GS} = 10V,$ $R_L = 1.25\Omega, R_G = 3\Omega,$
Turn-On Rise Time	t_r	—	16.5	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	26.1	—	ns	
Turn-Off Fall Time	t_f	—	5.6	—	ns	
Body Diode Reverse Recovery Time	t_{rr}	—	12.3	—	ns	$I_F = 12A, di/dt = 500A/\mu s$
Body Diode Reverse Recovery Charge	Q_{rr}	—	10.4	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - UIS in production with $L = 0.1mH$, starting $T_A = +25^\circ\text{C}$.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

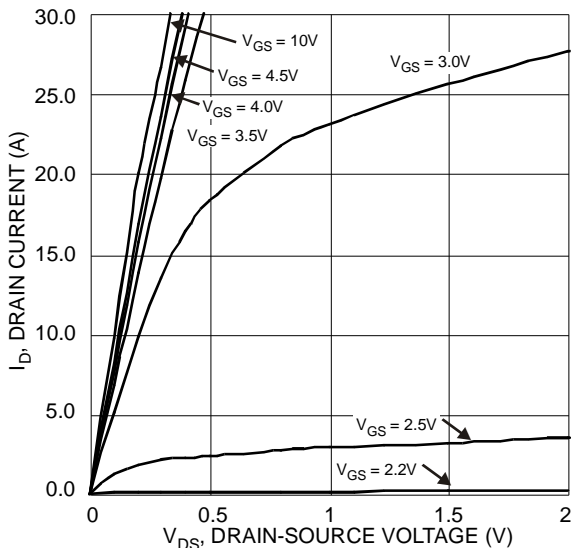


Figure 1 Typical Output Characteristic

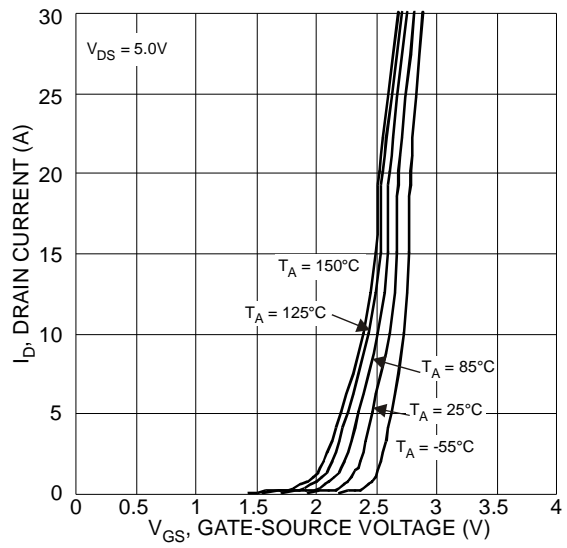


Figure 2 Typical Transfer Characteristics

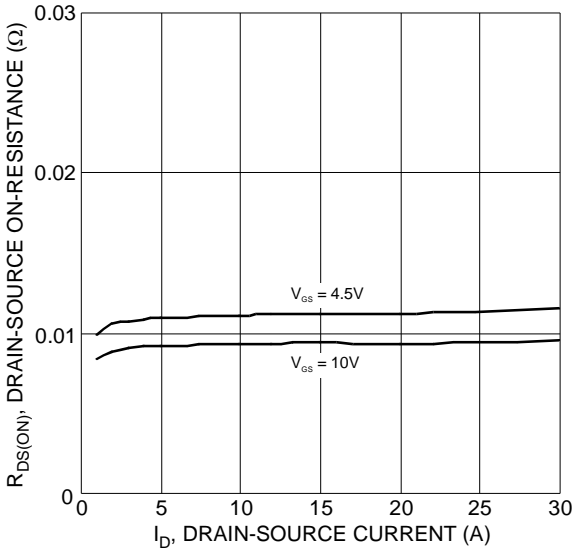


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

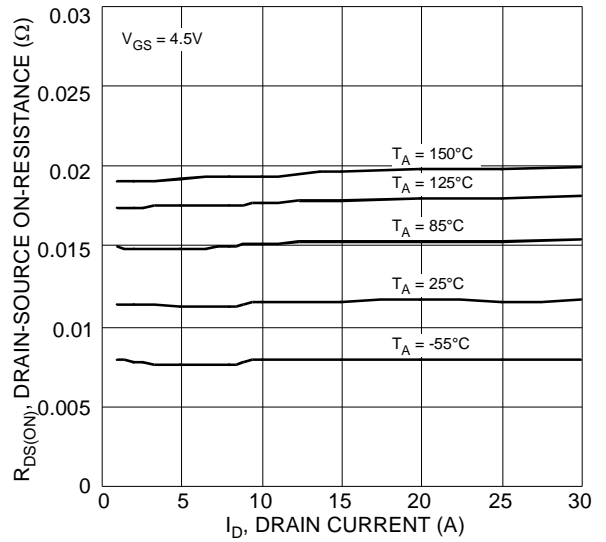


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

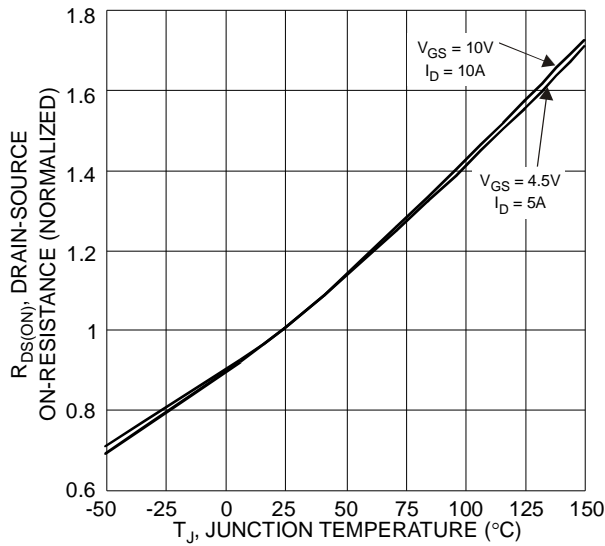


Figure 5 On-Resistance Variation with Temperature

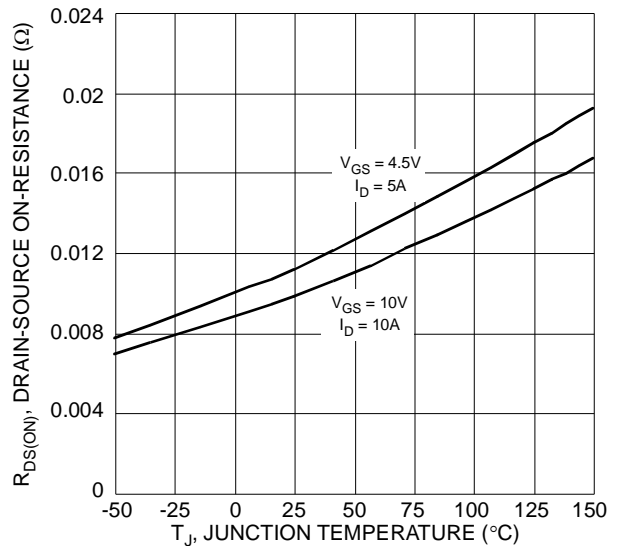


Figure 6 On-Resistance Variation with Temperature

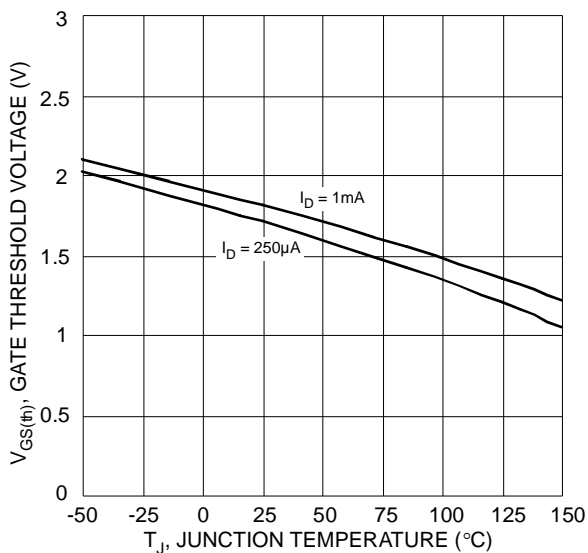


Figure 7 Gate Threshold Variation vs. Ambient Temperature

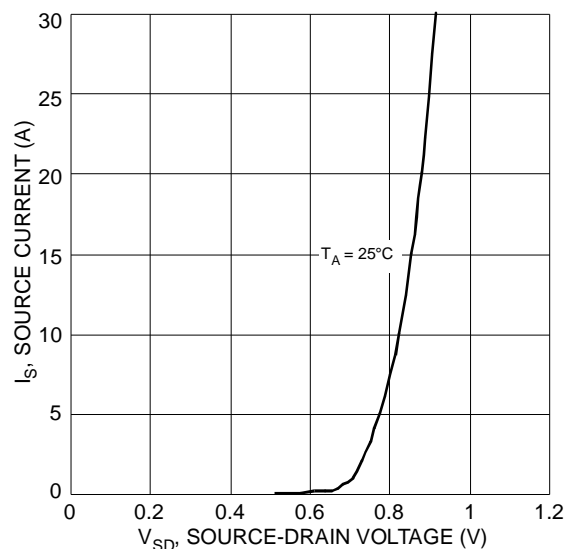


Figure 8 Diode Forward Voltage vs. Current

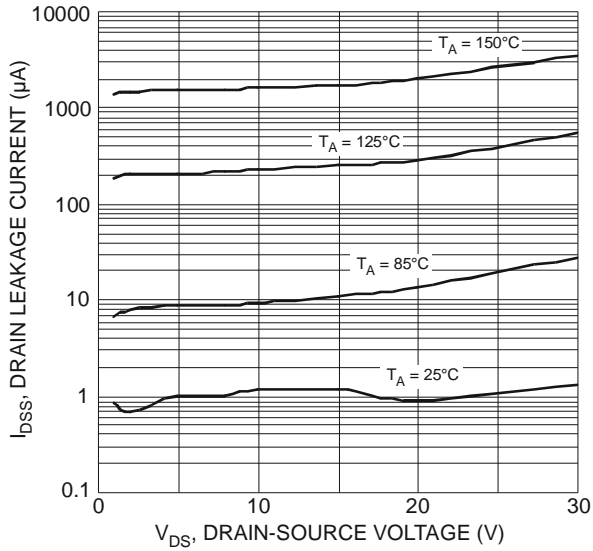


Figure 9 Typical Drain-Source Leakage Current vs. Voltage

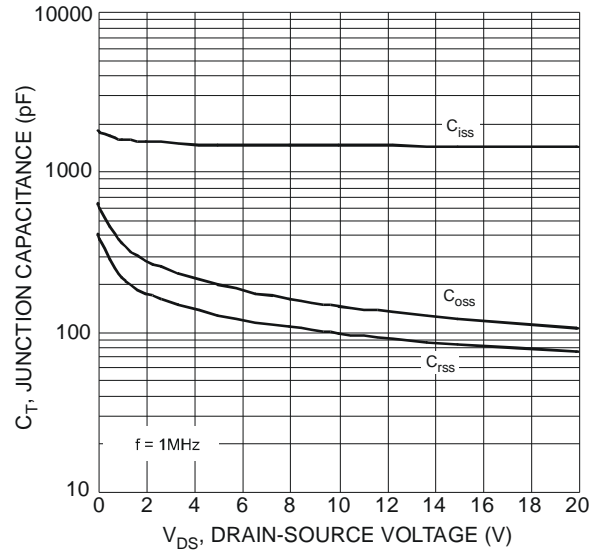


Figure 10 Typical Junction Capacitance

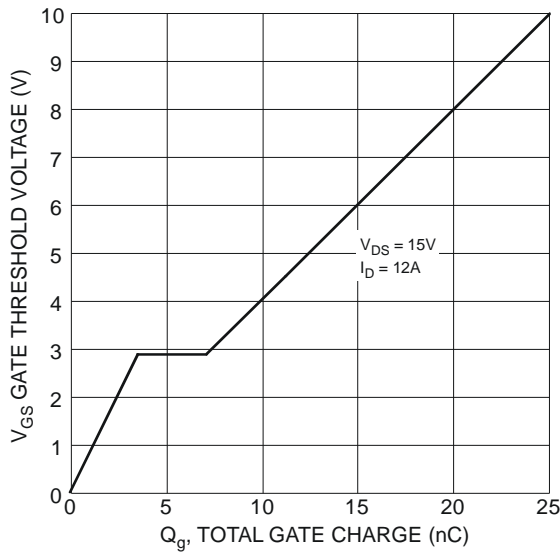


Figure 11 Gate Charge

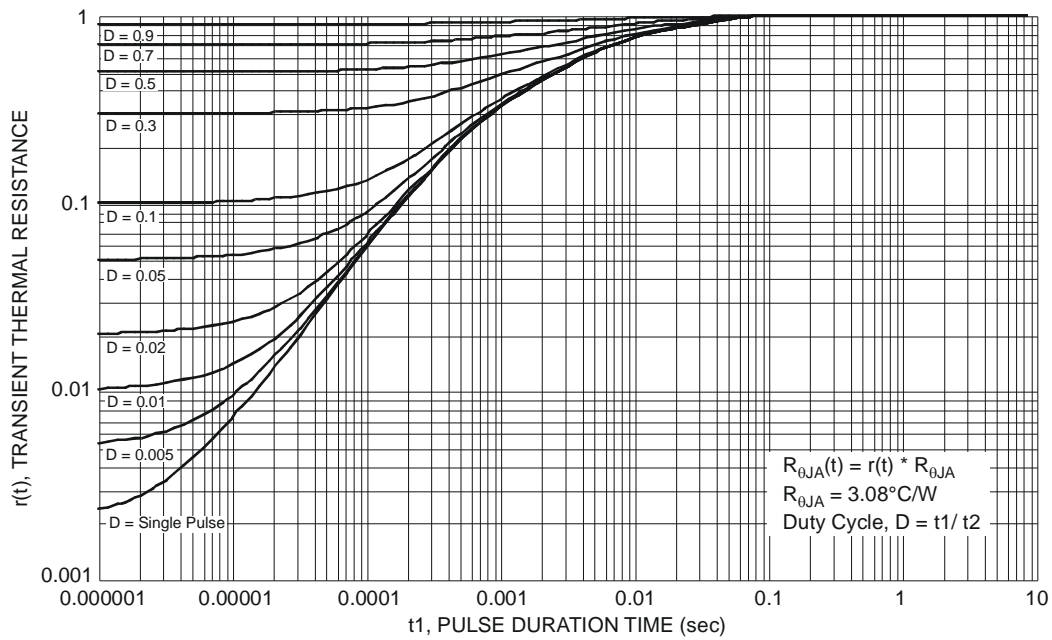
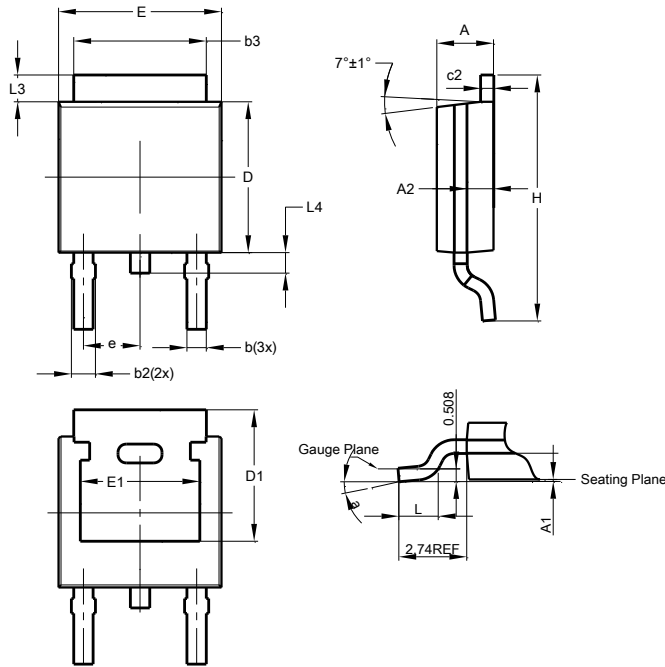


Figure 12 Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

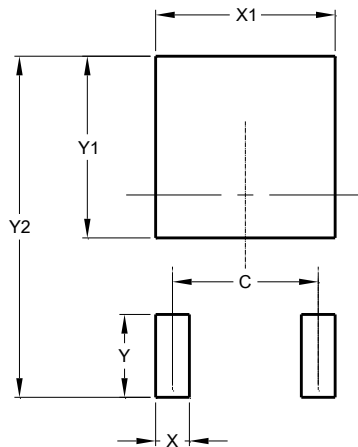


TO252			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c2	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	—	—
e	—	—	2.286
E	6.45	6.70	6.58
E1	4.32	—	—
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	—
All Dimensions in mm			

NEW PRODUCT

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.